

Fig. 4-27

The transfer characteristics of p type CW poly-Silicon TFTs. HF+O3 pre clean, laser power is 4W and scan speed is 7cm/sec, W/L = 6 μ m/12 μ m, $V_t(p2)$ -4.0V, $V_t(p1)$ -4.2V, $U_{fe}(p2)$ 206 cm²/V•sec, $U_{fe}(p1)$ 227 cm²/V•sec, $I_{off}(p1)$ 2.00E-14A, $I_{off}(p2)$ 1.87E-13A, SS(p1) 0.46, SS(p2) 0.41, on/off current ratio (p2) 1.0E+8 and on/off current ratio (p1) 1.1E+7

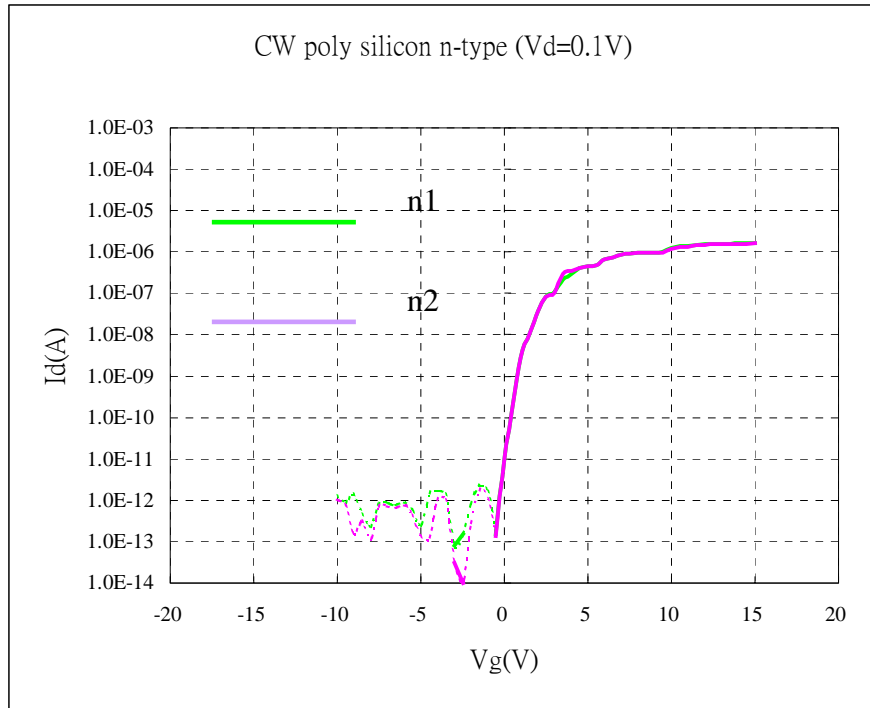


Fig. 4-28 The transfer characteristics of n type CW poly-Silicon TFTs. HF+O3 pre clean, laser power is 4W and scan speed is 7cm/sec, W/L = $6\mu\text{m}/12\mu\text{m}$, $V_t(n1)$ 7.6V, $V_t(n2)$ 7.3V, $U_{fe}(n1)$ 298 $\text{cm}^2/\text{V}\cdot\text{sec}$, $U_{fe}(n2)$ 257 $\text{cm}^2/\text{V}\cdot\text{sec}$, $I_{off}(n1)$ $2.05E-13\text{A}$, $I_{off}(n2)$ $1.72E-13\text{A}$, $SS(n1)$, $SS(n2)$ 0.37, on/off current ratio (n1) $6.6E+6$ and on/off current ratio (n2) $7.7E+6$